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20 V, single P-channel Trench MOSFET 20 July 2012

Product data sheet

1. Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- 3 kV ESD protected
- Trench MOSFET technology
- Low threshold voltage

1.3 Applications

- Relay driver
- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage	_		-8	-	8	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	-	-4	А
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I _D = -3.6 A; T _j = 25 °C		-	50	66	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		D
2	D	drain		
3	G	gate		G (T
4	S	source	TSOP6 (SOT457)	
5	D	drain		
6	D	drain	-	S 017aaa259

3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PMN50UPE	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457			

4. Marking

Table 4. Marking codes	
Type number	Marking code
PMN50UPE	WH

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	-4	А
		V_{GS} = -4.5 V; T_{amb} = 25 °C	[1]	-	-3.6	А
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-2.3	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-14.4	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	510	mW
			[1]	-	1235	mW
		T _{sp} = 25 °C		-	5000	mW

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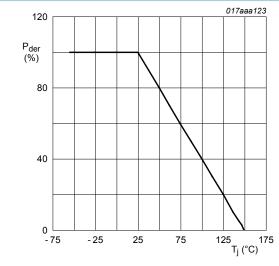
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Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain o	liode	·				,
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.3	А
ESD maximum rating						
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	3000	V

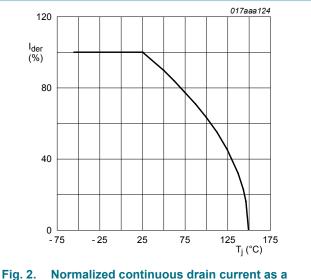
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
[3] Measured between all pins.





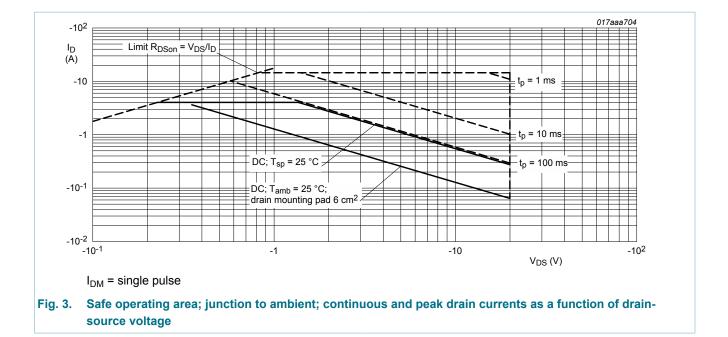
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$



Ig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^\circ \text{C})}} \times 100 \text{ \%}$$

20 V, single P-channel Trench MOSFET



6. Thermal characteristics

Table 6. Th	nermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fro	thermal resistance	in free air	[1]	-	213	245	K/W
	from junction to ambient		[2]	-	88	100	K/W
	ambient		[3]	-	70	81	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	21	25	K/W

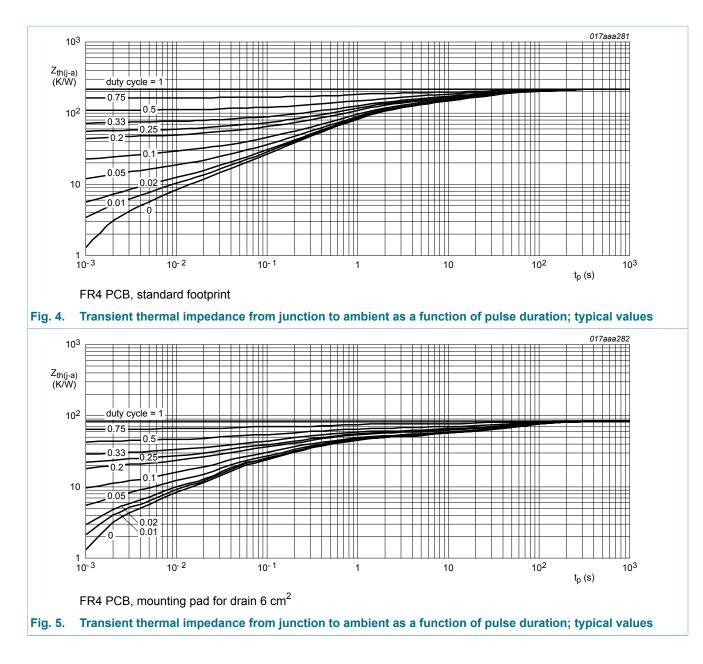
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm², t \leq 5 s.

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7. Characteristics

Table 7. Ch	aracteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C		-20	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C		-0.47	-0.6	-0.9	V
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C		-	-	-1	μA
		V _{DS} = -20 V; V _{GS} = 0 V; T _j = 150 °C		-	-	-10	μA
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 °C	-	-	10	μA
		V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I _D = -3.6 A; T _j = 25 °C	-	50	66	mΩ
	resistance	V _{GS} = -4.5 V; I _D = -3.6 A; T _j = 150 °C	-	73	96	mΩ
		V _{GS} = -2.5 V; I _D = -2.1 A; T _j = 25 °C	-	57	81	mΩ
		V _{GS} = -1.8 V; I _D = -2.1 A; T _j = 25 °C	-	70	110	mΩ
9 _{fs}	forward transconductance	V _{DS} = -5 V; I _D = -3.6 A; T _j = 25 °C	-	18	-	S
Dynamic cl	naracteristics	· · · ·				
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -3.2 A; V_{GS} = -4.5 V;	-	10.5	15.7	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	2.2	-	nC
Q _{GD}	gate-drain charge		-	2.7	-	nC
C _{iss}	input capacitance	V_{DS} = -10 V; f = 1 MHz; V_{GS} = 0 V;	-	24	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	106	-	pF
C _{rss}	reverse transfer capacitance		-	14.6	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I _D = -3.6 A; V _{GS} = -4.5 V;	-	400	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	700	-	ns
t _{d(off)}	turn-off delay time		-	2180	-	ns
t _f	fall time		-	8800	-	ns

Source-drain diode

source-drain voltage

 V_{SD}

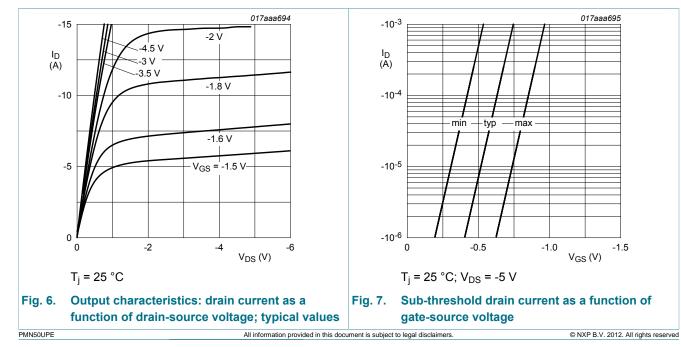
 I_{S} = -1.3 A; V_{GS} = 0 V; T_{j} = 25 °C

-1.2

V

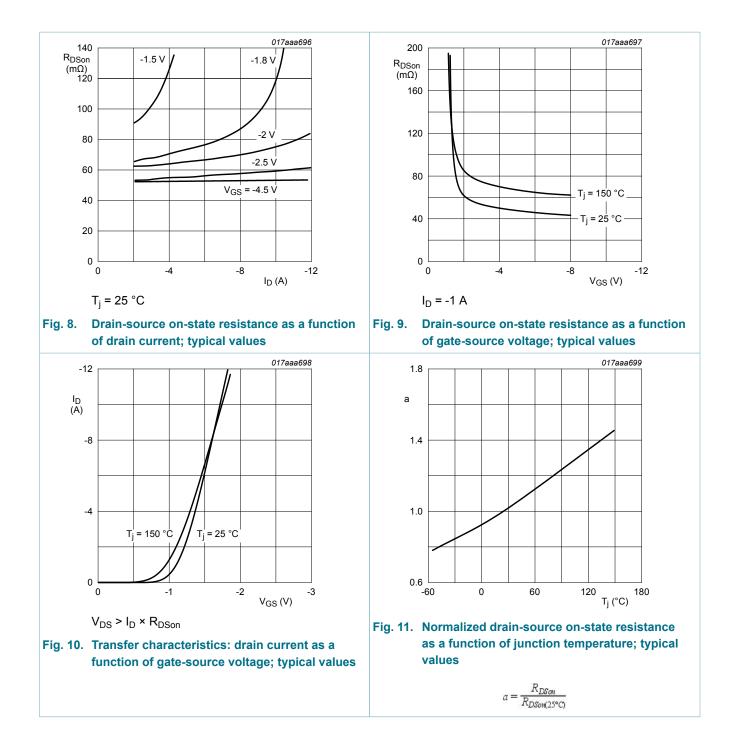
-0.8

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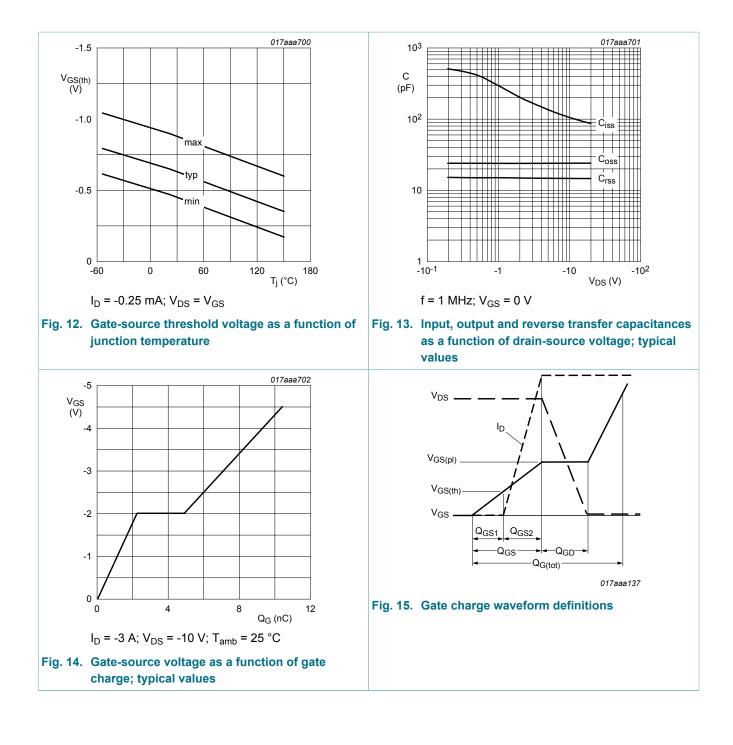
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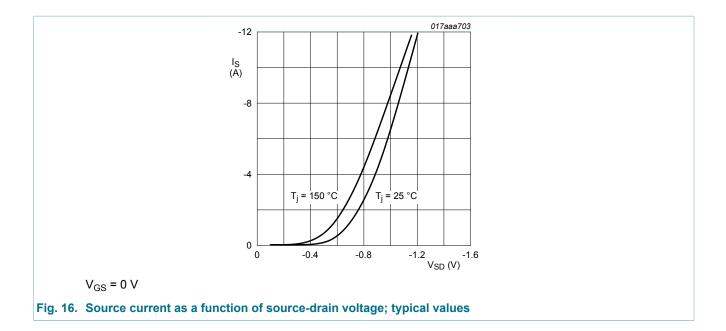
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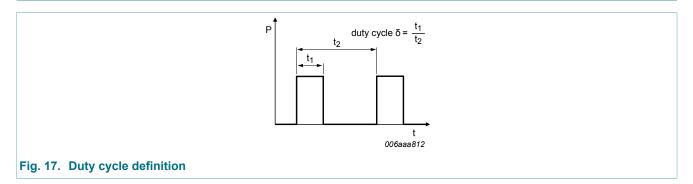


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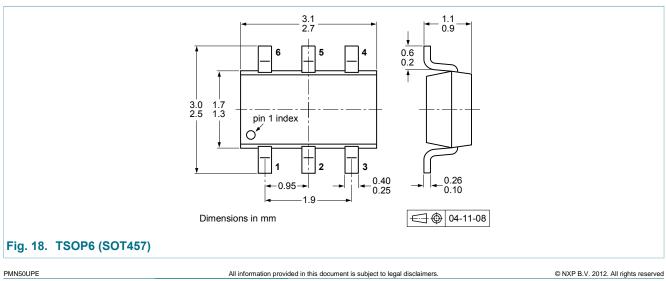
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8. Test information

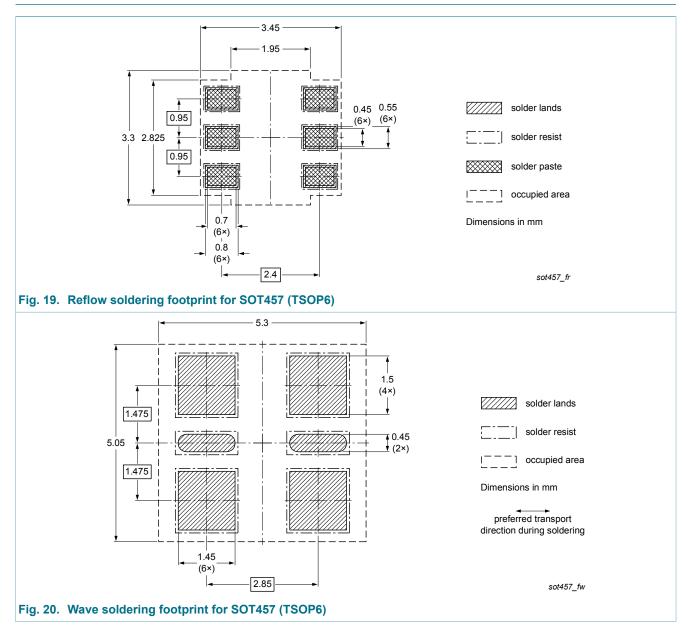


9. Package outline



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10. Soldering



11. Revision history

Table 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PMN50UPE v.1	20120720	Product data sheet	-	-	

20 V, single P-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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